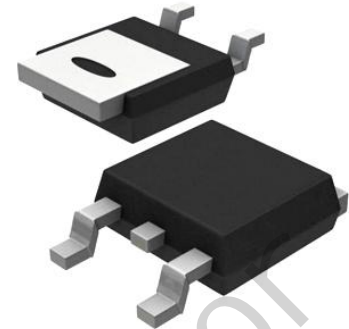


Description:

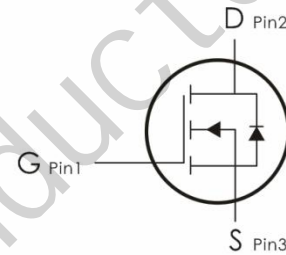
This N-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.



Features:

- 1) $V_{DS}=60V, I_D=30A, R_{DS(ON)} < 30m\ \Omega @ V_{GS}=10V$
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra low $R_{DS(ON)}$.
- 5) Excellent package for good heat dissipation.



Absolute Maximum Ratings: ($T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current- $T_C=25^\circ C$	30	A
	Continuous Drain Current- $T_C=100^\circ C$	16	
I_{DM}	Drain Current - Pulsed1	100	A
E_{AS}	Single Pulse Avalanche Energy (note1)	24	mJ
I_{AS}	Avalanche Current (note2)	22	A
P_D	Power Dissipation	40	W
	Power Dissipation - Derate above $25^\circ C$	0.32	W/ $^\circ C$
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ C$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	3.1	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62	

Electrical Characteristics: ($T_c=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\ \mu\text{A}$	60	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BVDSS Temperature Coefficient	Reference to 25°C , $I_D=1\text{mA}$	---	0.07	---	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS}=0V, V_{DS}=650V$	---	---	1	μA
		$V_{GS}=0V, V_{DS}=480V, T_J=125^\circ\text{C}$	---	---	10	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 30V, V_{DS}=0A$	---	---	± 100	nA
On Characteristics						
$V_{GS(th)}$	GATE-Source Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\ \mu\text{A}$	1.2	1.7	2.5	V
$R_{DS(on)}$	Drain-Source On Resistance	$V_{GS}=10V, I_D=15A$	---	25	30	m Ω
		$V_{GS}=4.5V, I_D=10A$	---	31	40	m Ω
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=25V, V_{GS}=0V, f=1\text{MHz}$	---	1150	1700	pF
C_{oss}	Output Capacitance		---	60	90	
C_{rss}	Reverse Transfer Capacitance		---	43	65	
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time ^{2,3}	$V_{DD}=30V, I_D=1A,$ $R_G=6\ \Omega$ (Note 3,4)	---	15	40	ns
t_r	Rise Time ^{2,3}		---	4.5	8	ns
$t_{d(off)}$	Turn-Off Delay Time ^{2,3}		---	27	50	ns

t_f	Fall Time ^{2,3}		---	7.5	13	ns
Q_g	Total Gate Charge ^{2,3}		---	16	20	nC
Q_{gs}	Gate-Source Charge ^{2,3}	$V_{GS}=30V, V_{DS}=10V,$	---	2	4	nC
Q_{gd}	Gate-Drain "Miller" Charge ^{2,3}	$I_D=20A(\text{Note } 3,4)$	---	3.5	7	nC
Drain-Source Diode Characteristics						
V_{SD}	Diode Forward Voltage	$V_{GS}=0V, I_S=1A,$	---	---	1	V
I_S	Continuous Source Current	---	---	---	25	A
I_{SM}	Pulsed Source Current	---	---	---	100	A
T_{rr}	Reverse Recovery Time	$V_{GS}=0V, I_S=1A,$	---	17	---	ns
Q_{rr}	Reverse Recovery Charge	$di/dt=100A/\mu s(\text{Note } 3)$	---	12	---	nC

Notes:

- 1.Repetitive Rating : Pulsed width limited by maximum junction temperature.
- 2.VDD=25V,VGS=10V,L=0.1mH,IAS=22A.,RG=25 ,Starting TJ=25°C
- 3.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 4.Essentially independent of operating temperature.

Typical Characteristics: (T_c=25°C unless otherwise noted)

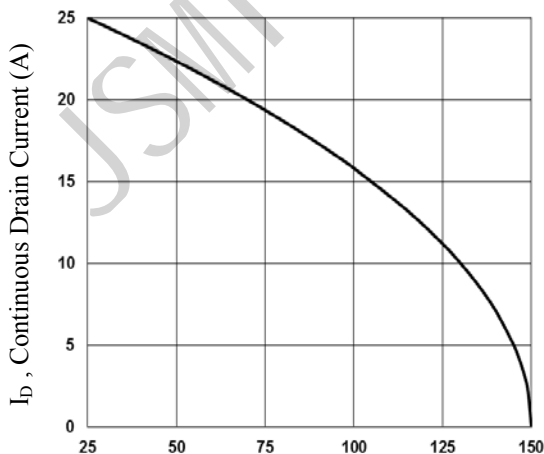


Fig.1 Continuous Drain Current vs. T_c

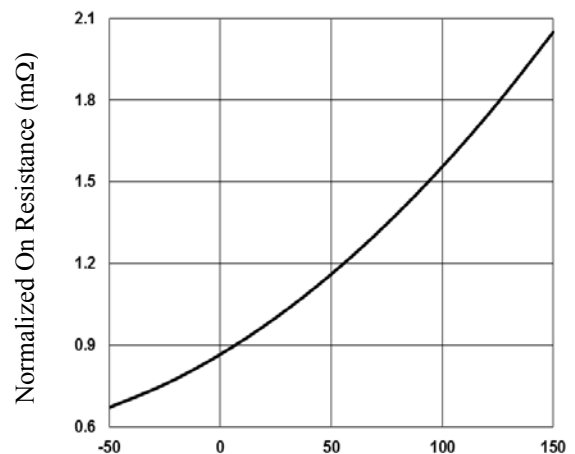


Fig.2 Normalized R_{DS(on)} vs. T_j

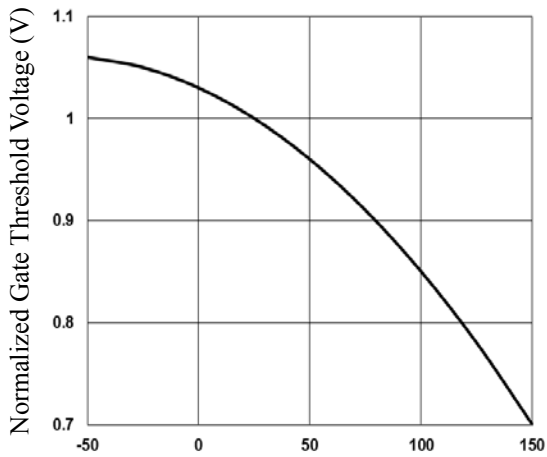
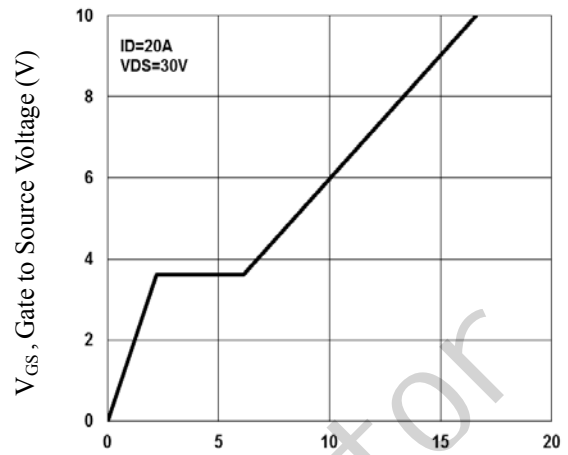

 Fig.3 Normalized V_{th} vs. T_j


Fig.4 Gate Charge Waveform

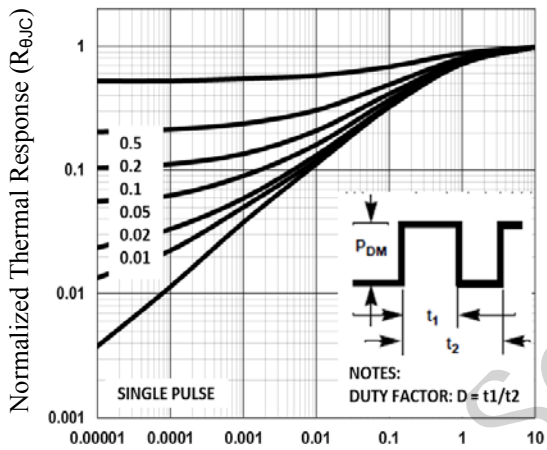


Fig.5 Normalized Transient Impedance

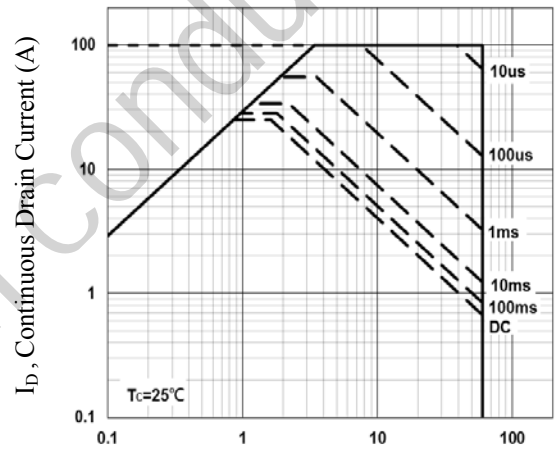


Fig.6 Maximum Safe Operation Area

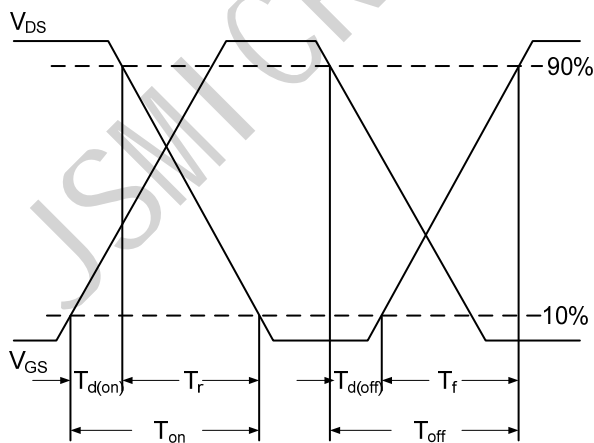


Fig.7 Switching Time Waveform

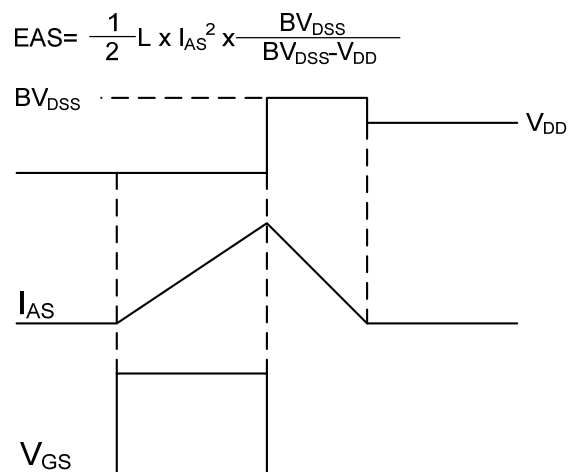


Fig.8 EAS Waveform

外形尺寸图 / Package Dimensions

